

**INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION**

(PTO-1449)

ATTY. DOCKET NO.
50432-477

SERIAL NO.

~~Unassigned~~

10/02/497

APPLICANT

William G. EN, t al.

FILING DATE

~~Concurrently
Herewith~~

12/19/01

GROUP

~~Unassigned~~

2822

JC580 U.S. PTO
10/02/497

12/19/01

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
WGS	0,016,383A1	09/23/01	Chen et al.	438	243	
	6,180,490B1	01/30/01	Vassiliev et al.	438	424	
	6,300,172B1	10/09/01	Ang et al.	438	149	
	6,207,530B1	03/27/01	Hsu et al.	438	404	
WGS	5,851,891	12/22/98	Dawson et al.	438	303	

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

WGS	Shallow Trench Isolation, "Trench Isolation," http://courses.nus.edu.sg/course/phy/ > pgs. 1-4
	Institute of Microelectronics - Deep Submicron - Ultra-thin gate oxides, "Deep Submicron", http://www.ime.org.sg/deep/deep_ultra.htm/ >, pgs. 1-2
	SNP Applications/Shallow Trench Isolation (STI), "SNP 9000 Applications", http://www.surfaceinterface.com/snapappsSTI.html >, pgs. 1-2
	EXAMINER: <i>[Signature]</i> DATE CONSIDERED 11/16/02

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

